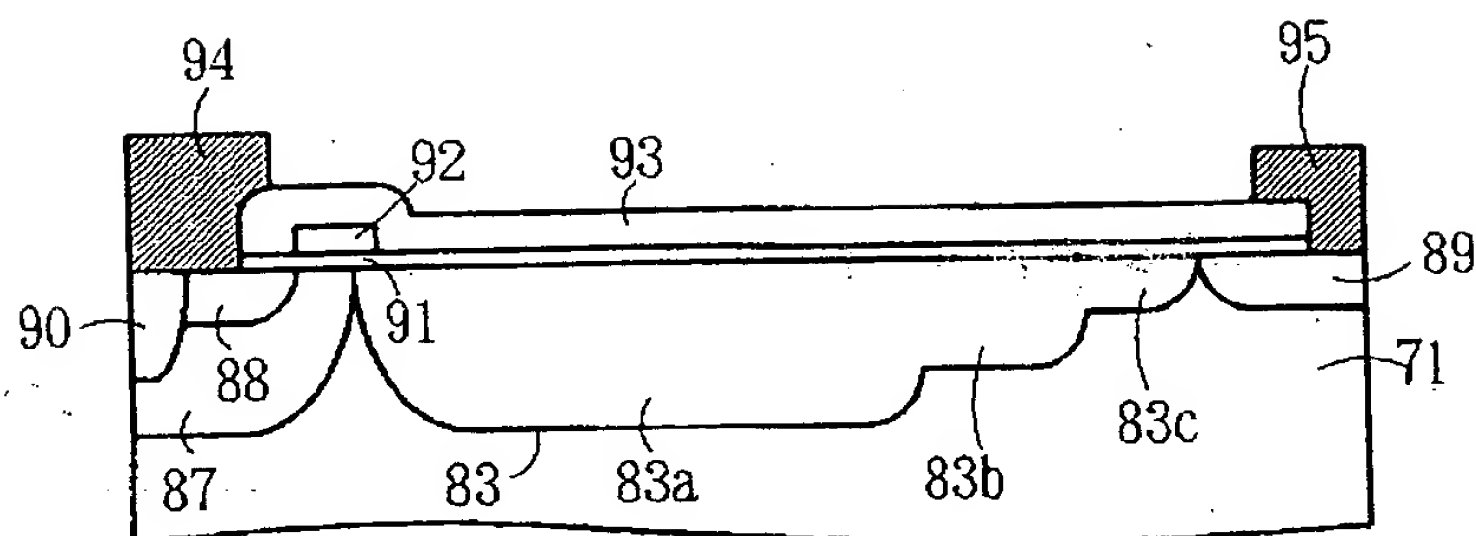


Fig. 1



- | | |
|-------------------------------|---|
| 71: n-type silicon substrate | 89: n-type drain region |
| 83: p-type offset region | 90: p ⁺ -type contact region |
| 83a: First p-type sub-region | 91: Gate insulation film |
| 83b: Second p-type sub-region | 92: Gate electrode |
| 83c: Third p-type sub-region | 93: Insulation film |
| 87: p-type base region | 94: Source electrode |
| 88: n-type source region | 95: Drain electrode |

Fig. 2

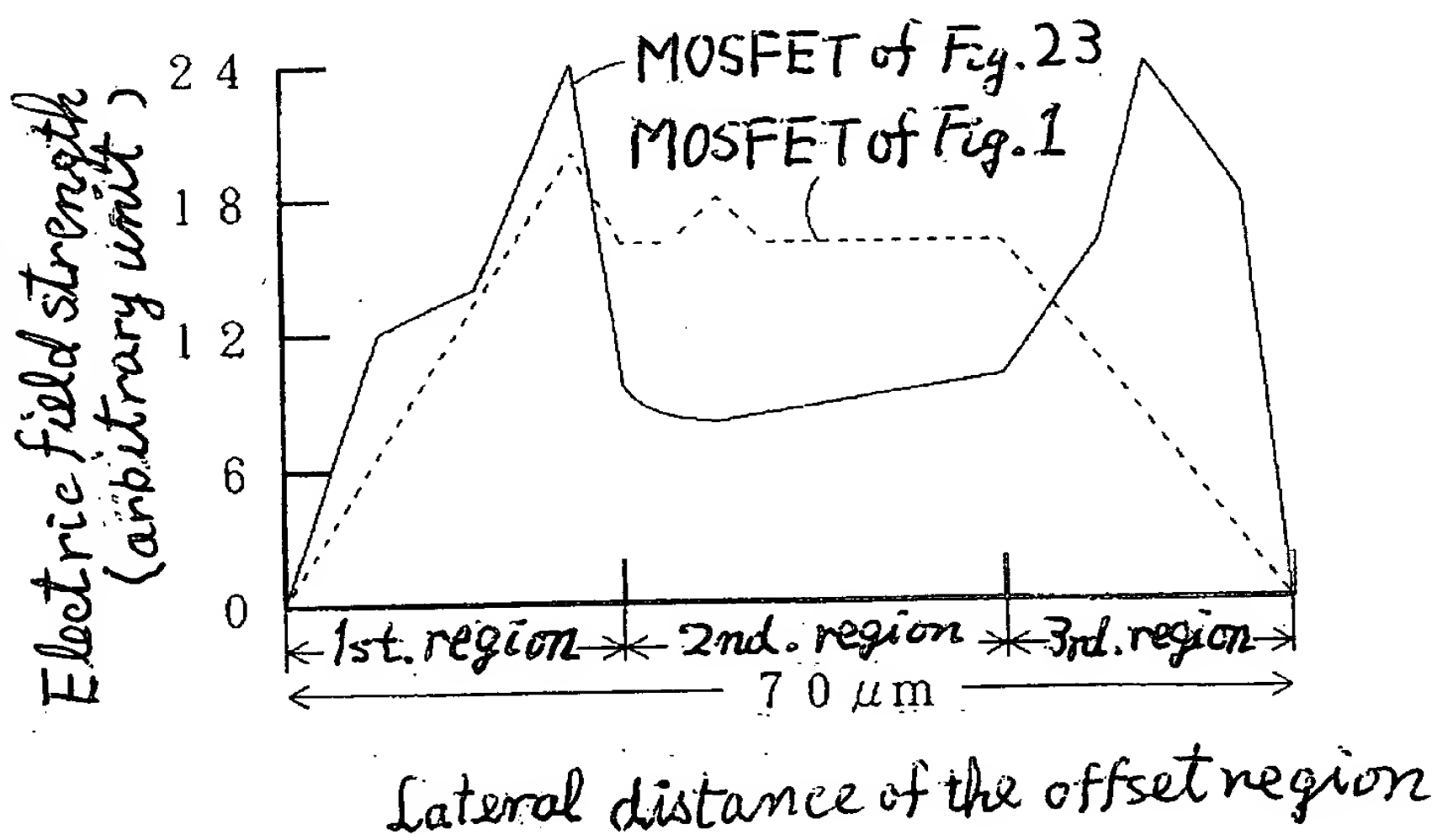


Fig. 3

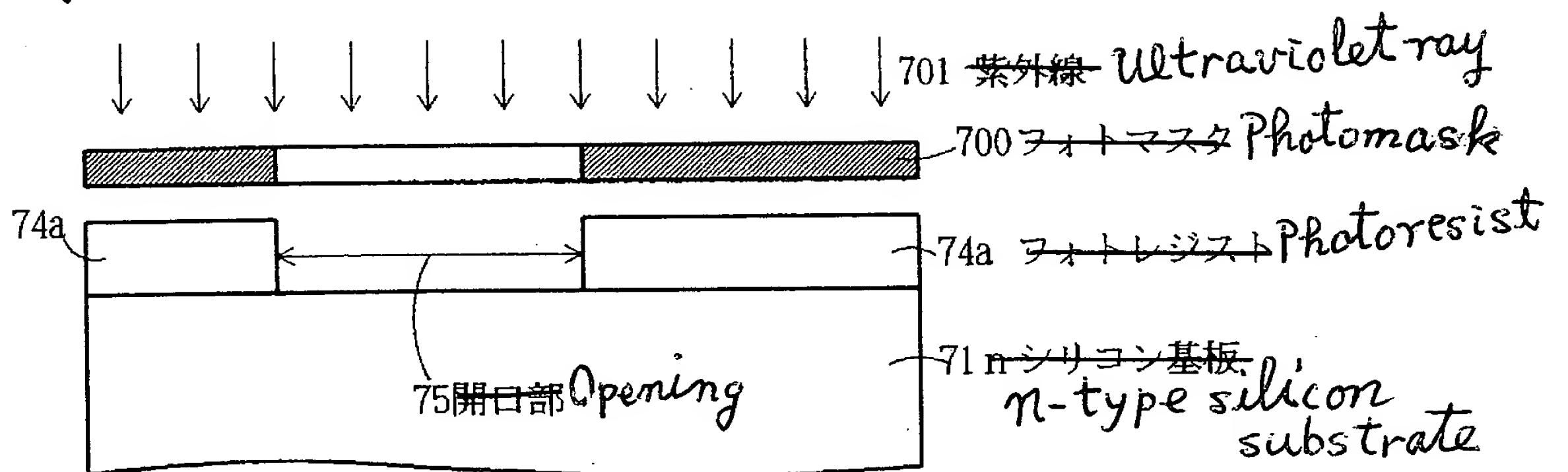


Fig. 4

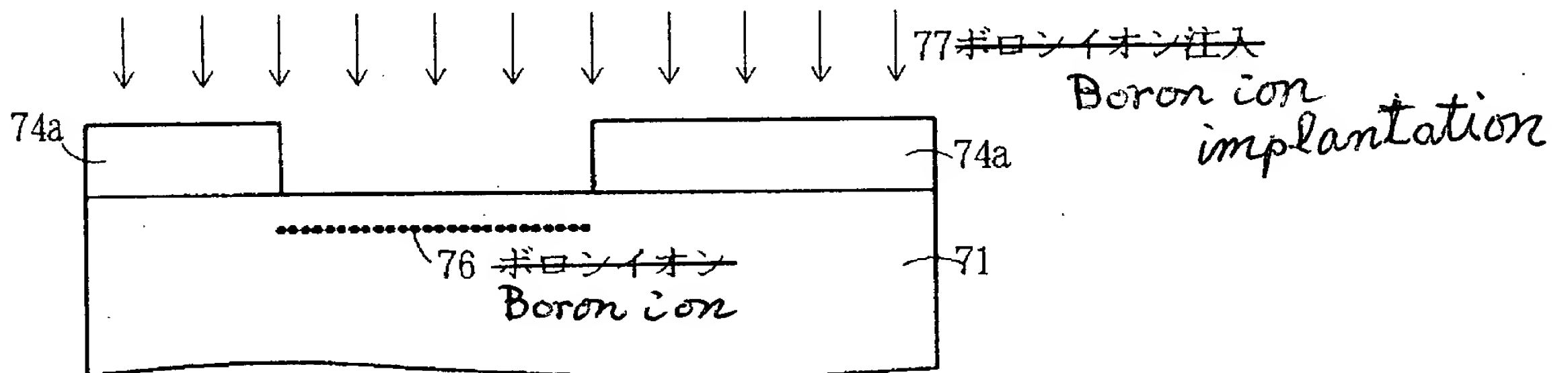


Fig. 5

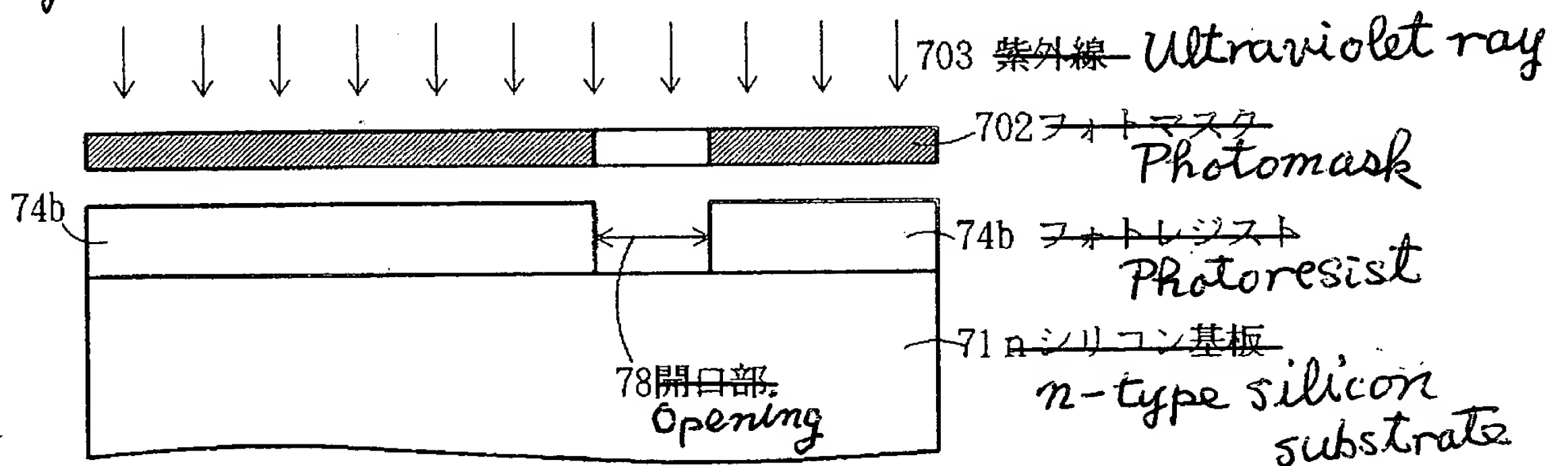


Fig. 6

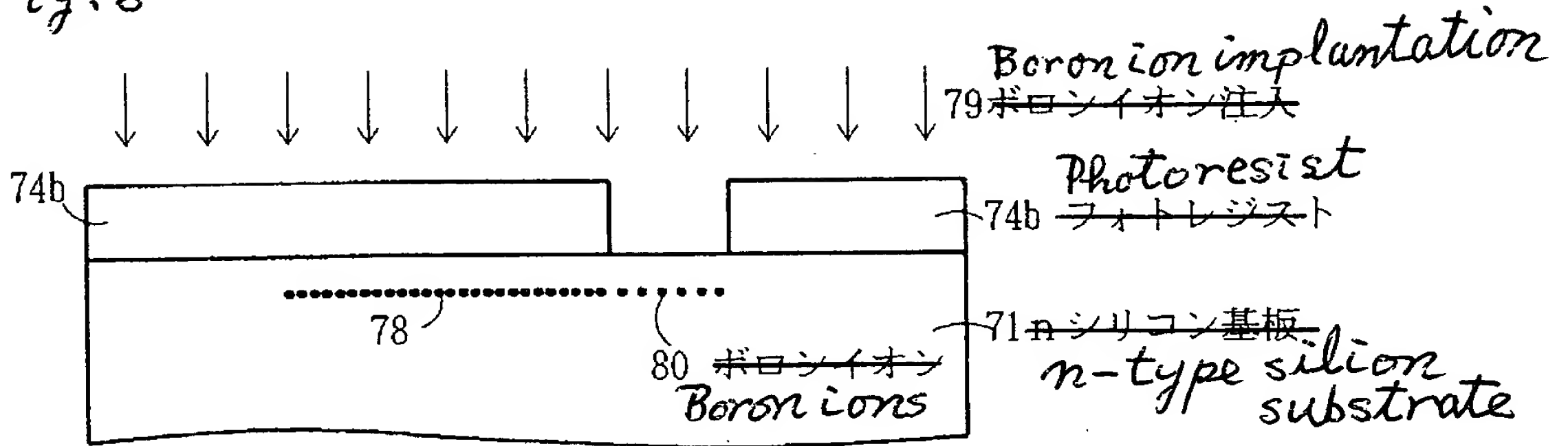


Fig. 7

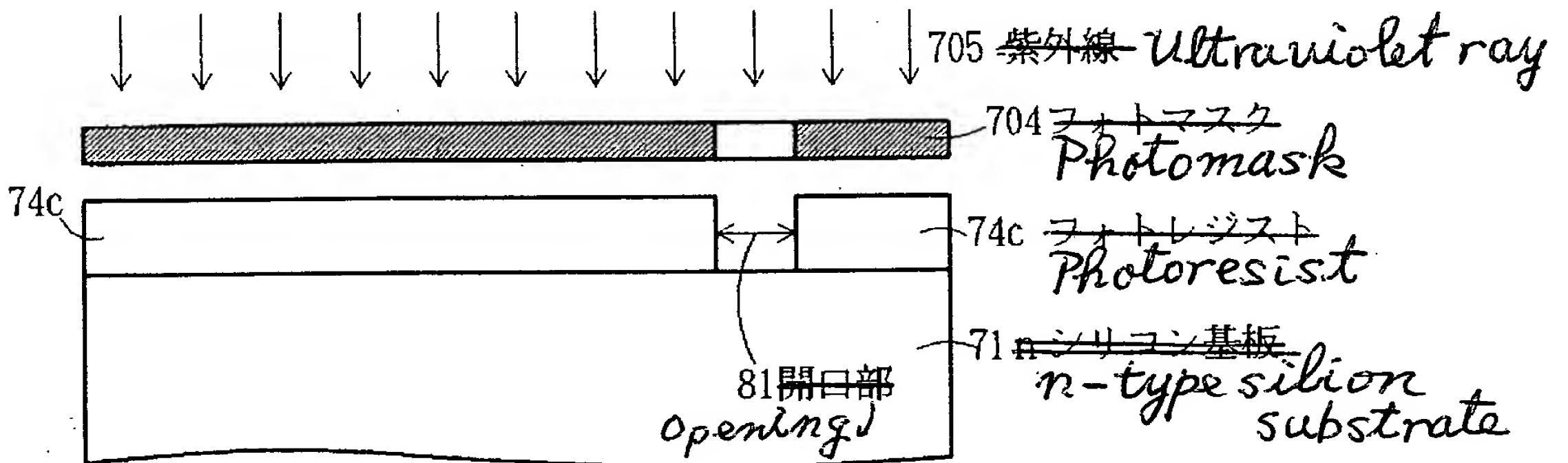


Fig. 8

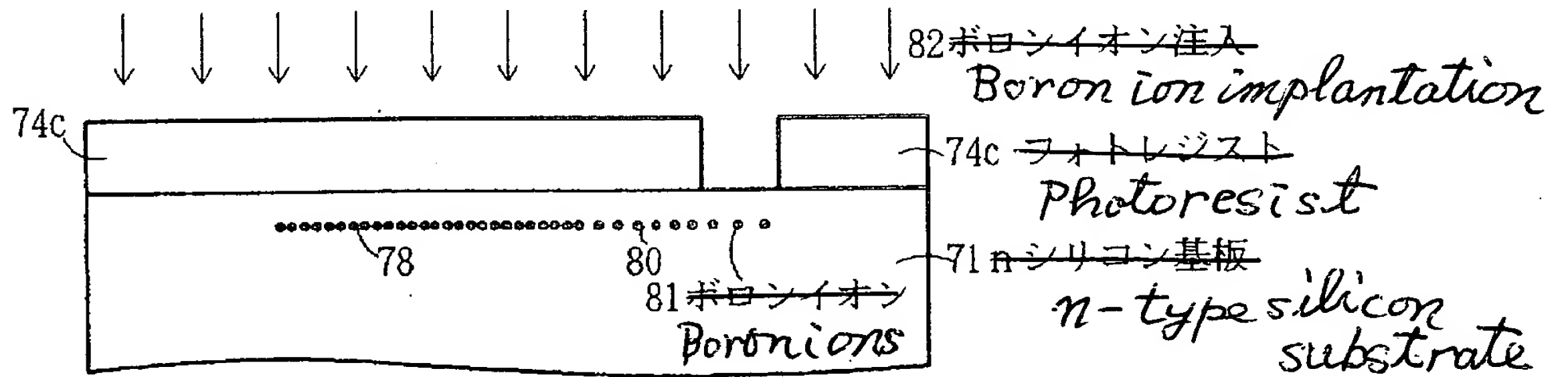


Fig. 9

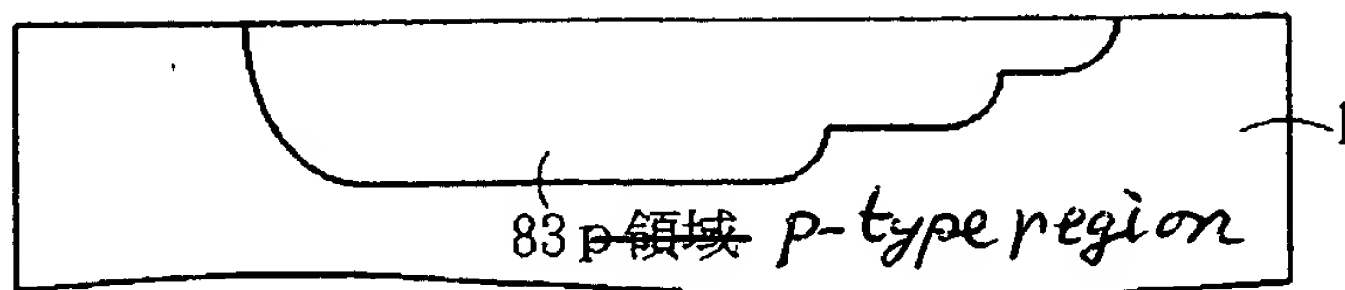


Fig. 10

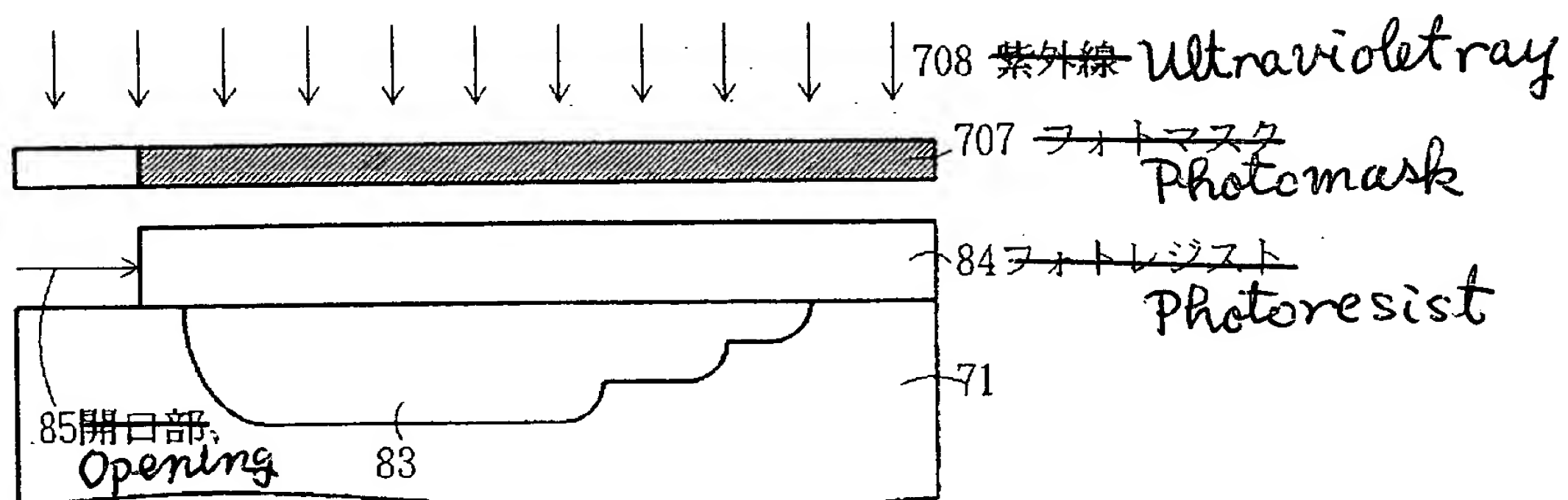


Fig. 11

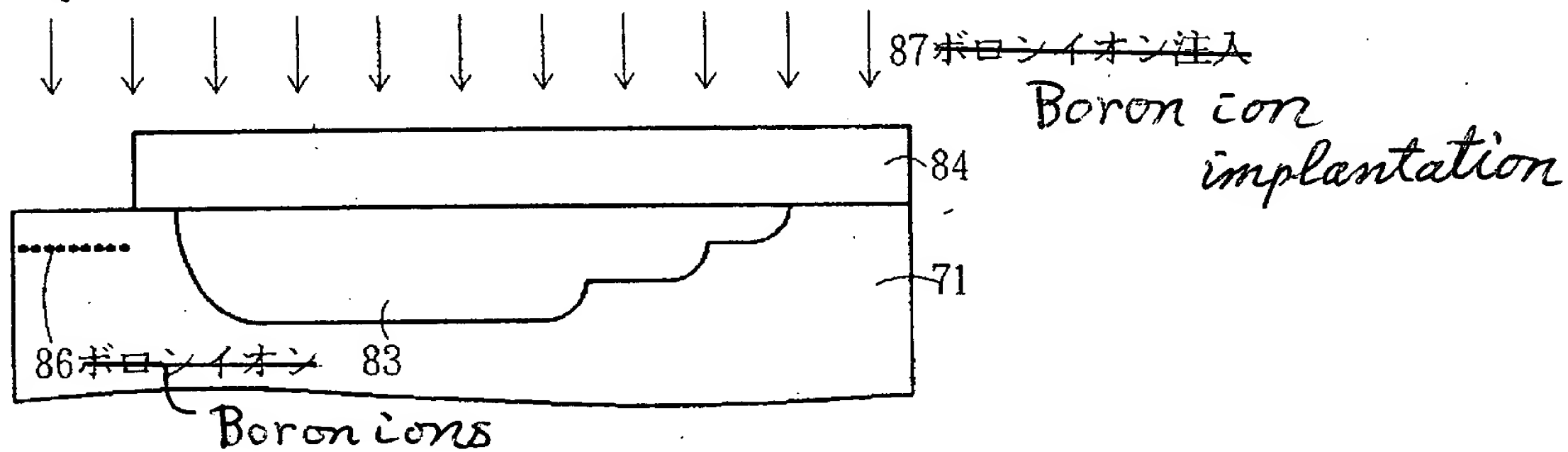


Fig. 12

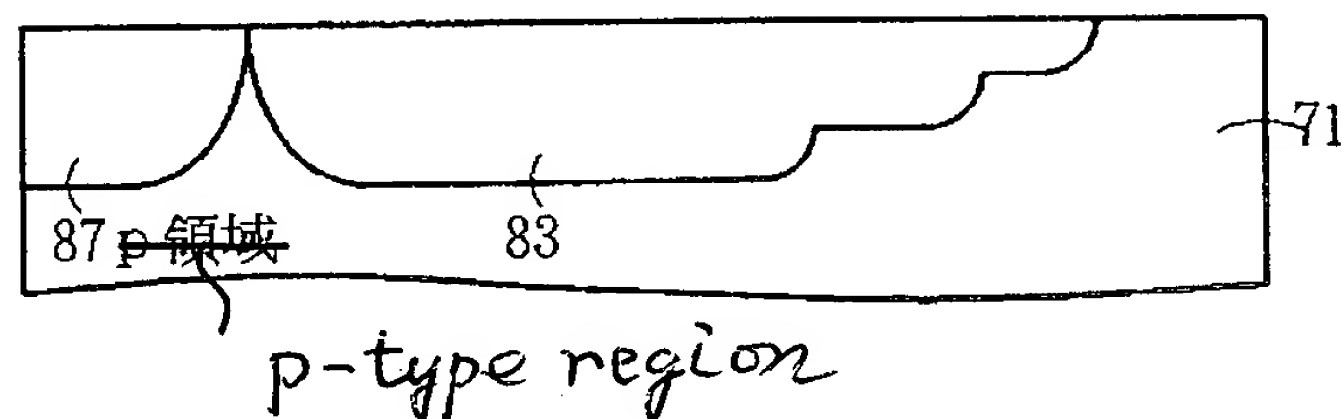
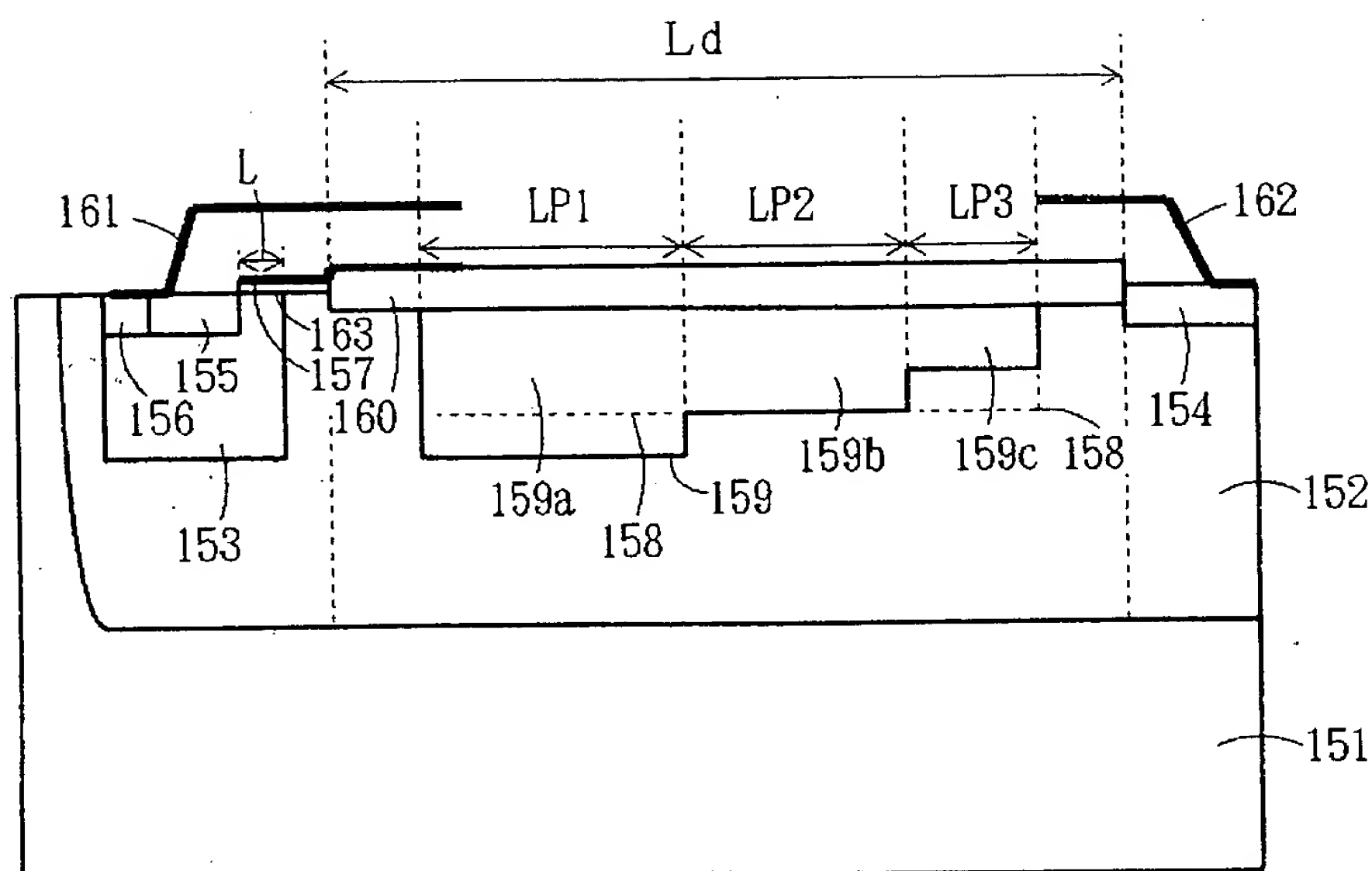


Fig. 13



- 151: p-type substrate
- 152: n-type well region
- 153: p-type base region
- 154: n-type drain region
- 155: n-type source region
- 156: p⁺-type contact region
- 157: Gate electrode
- 158: Boron diffusion depth
- 159: p-type diffusion region (p-type offset region)
- 159a: First p-type sub-region
- 159b: Second p-type sub-region
- 159c: Third p-type sub-region
- 160: Insulation film
- 161: Source electrode
- 162: Drain electrode
- 163: Gate insulation film

Fig. 14

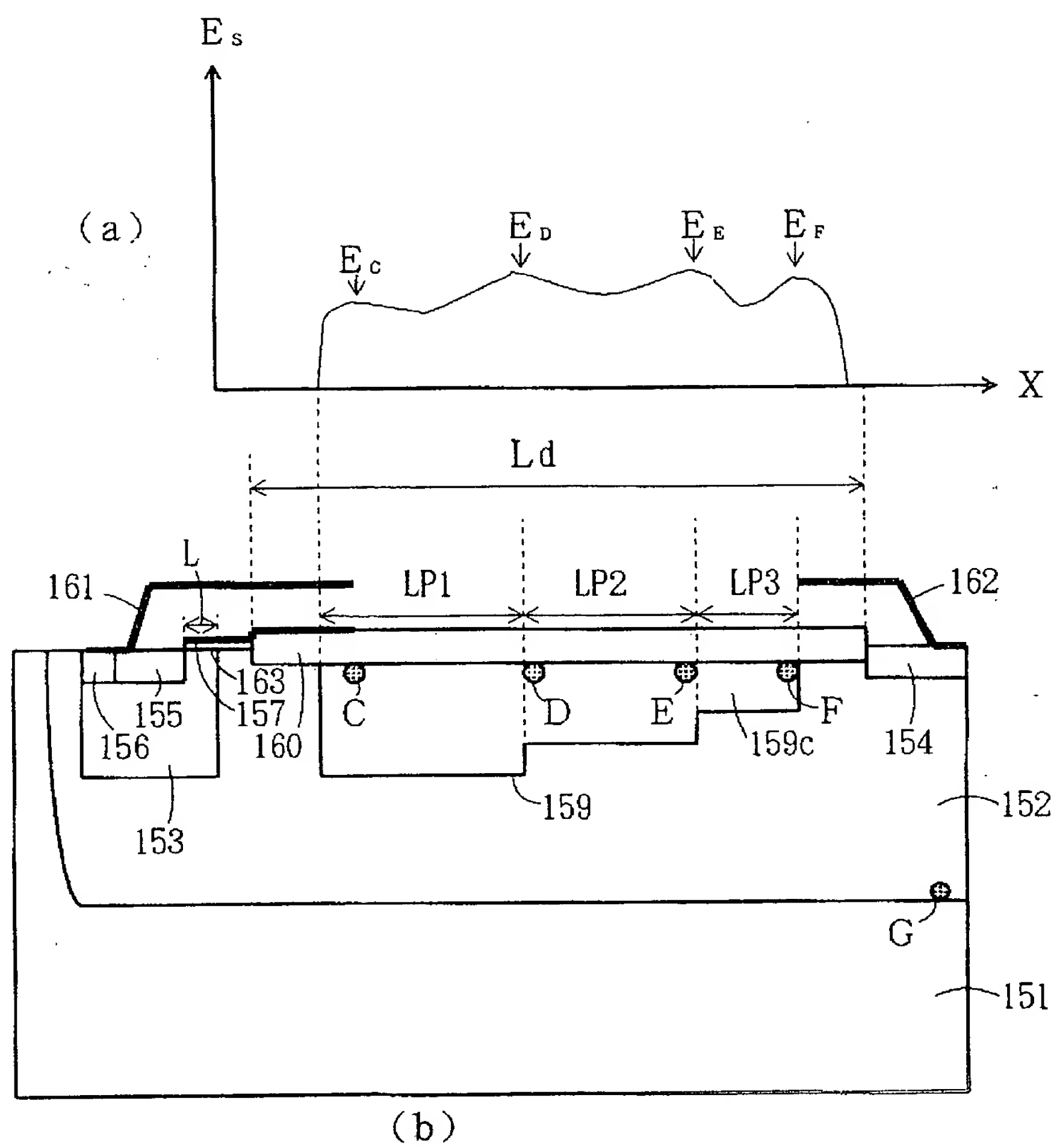
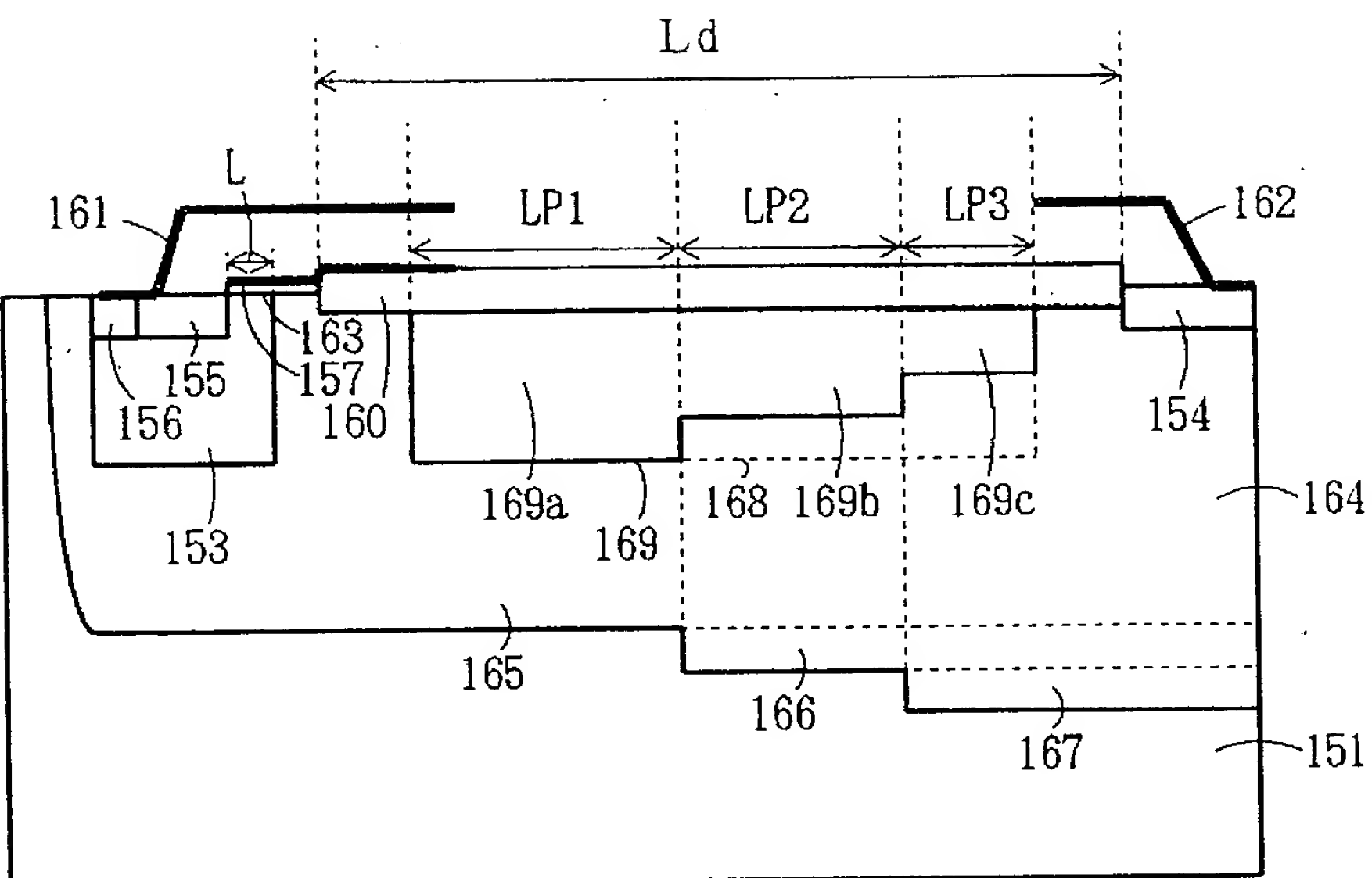


Fig. 15



- 164: n-type well region
165: First well sub-region
166: Second well sub-region
167: Third well sub-region
168: Boron diffusion depth
169: p-type diffusion region
169a: First p-type sub-region
169b: Second p-type sub-region
169c: Third p-type sub-region

Fig. 16(a)

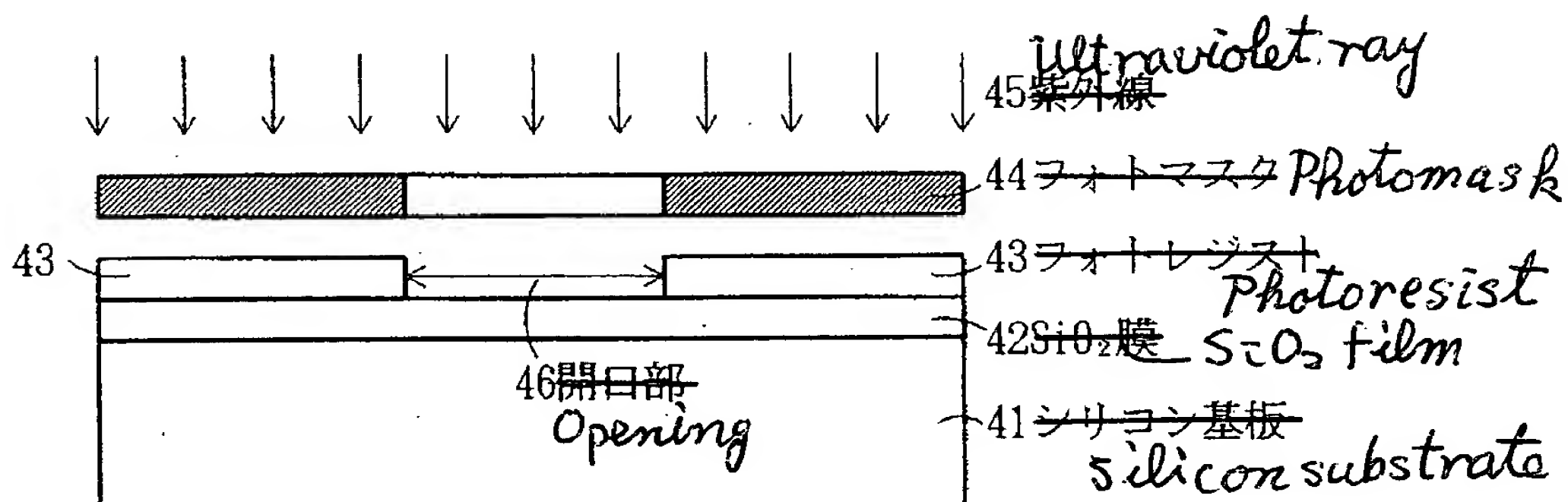


Fig. 16(b)

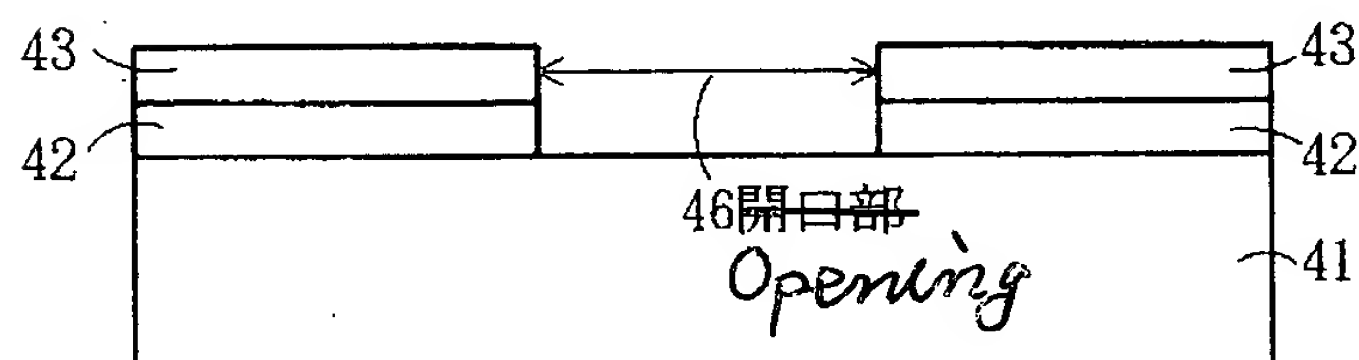


Fig. 16(c)

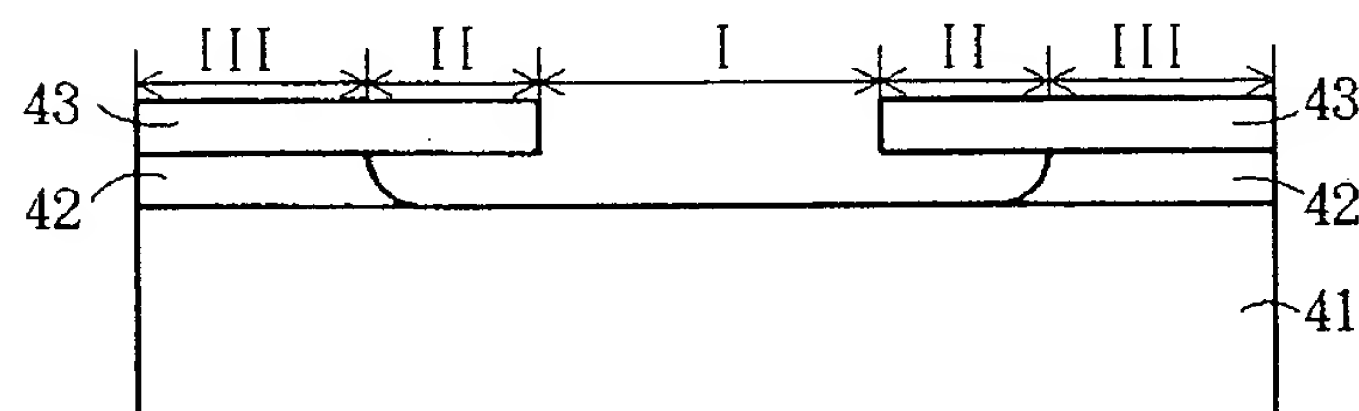


Fig. 16(d)

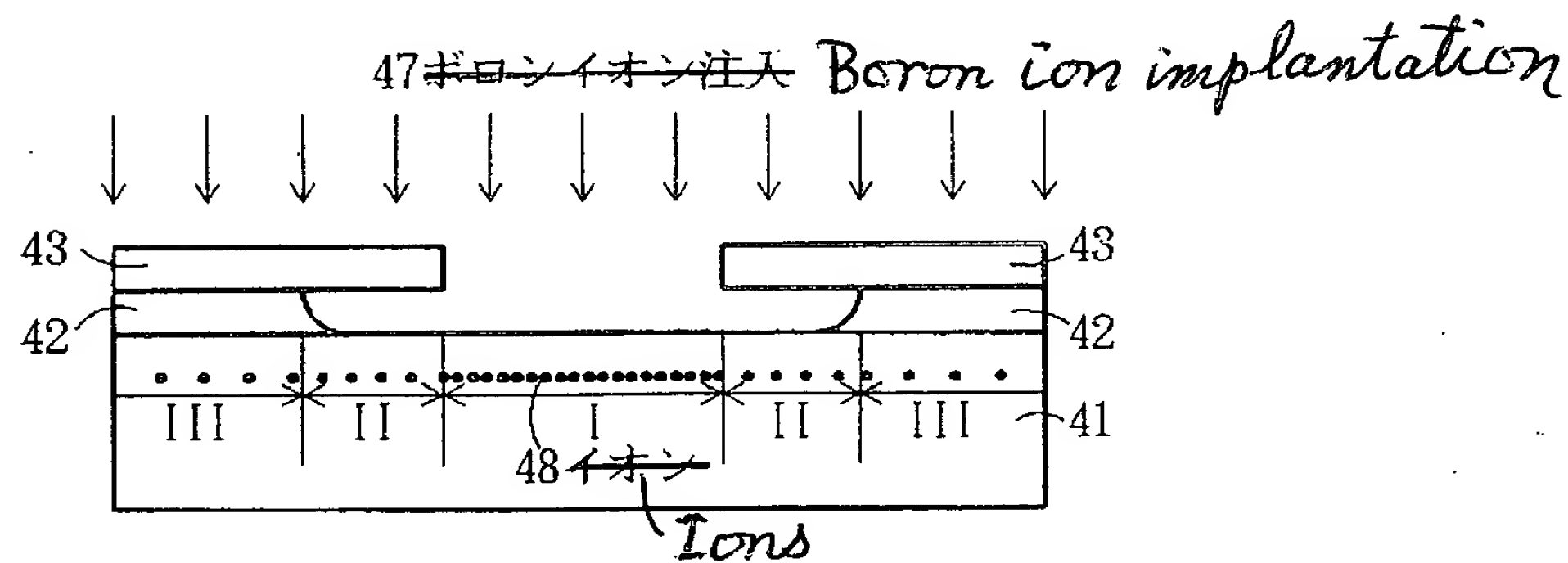


Fig. 16(e)

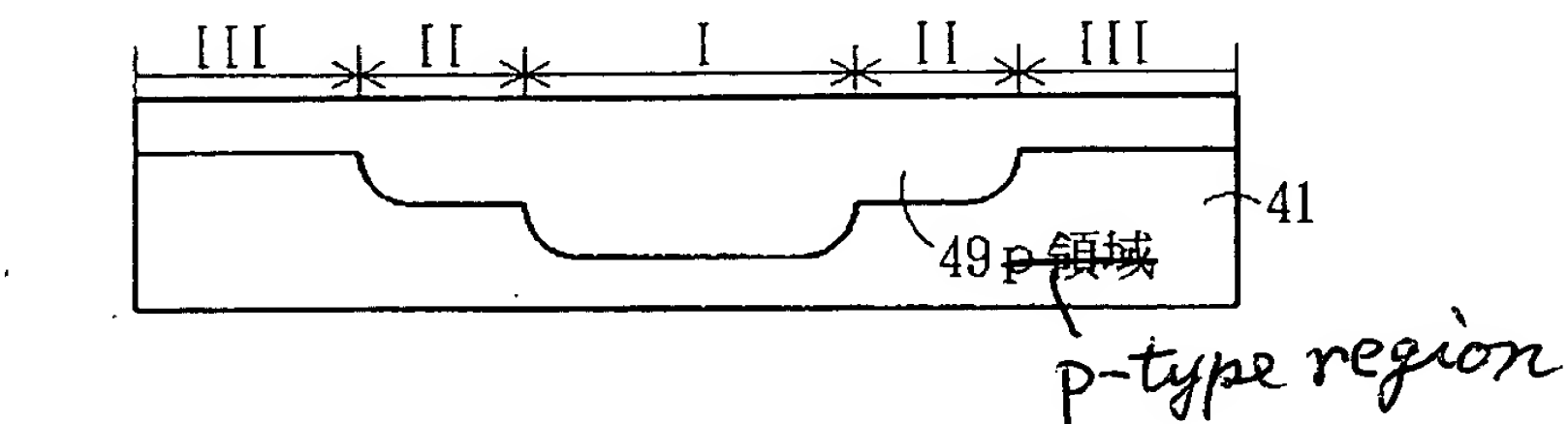


Fig.17(a)

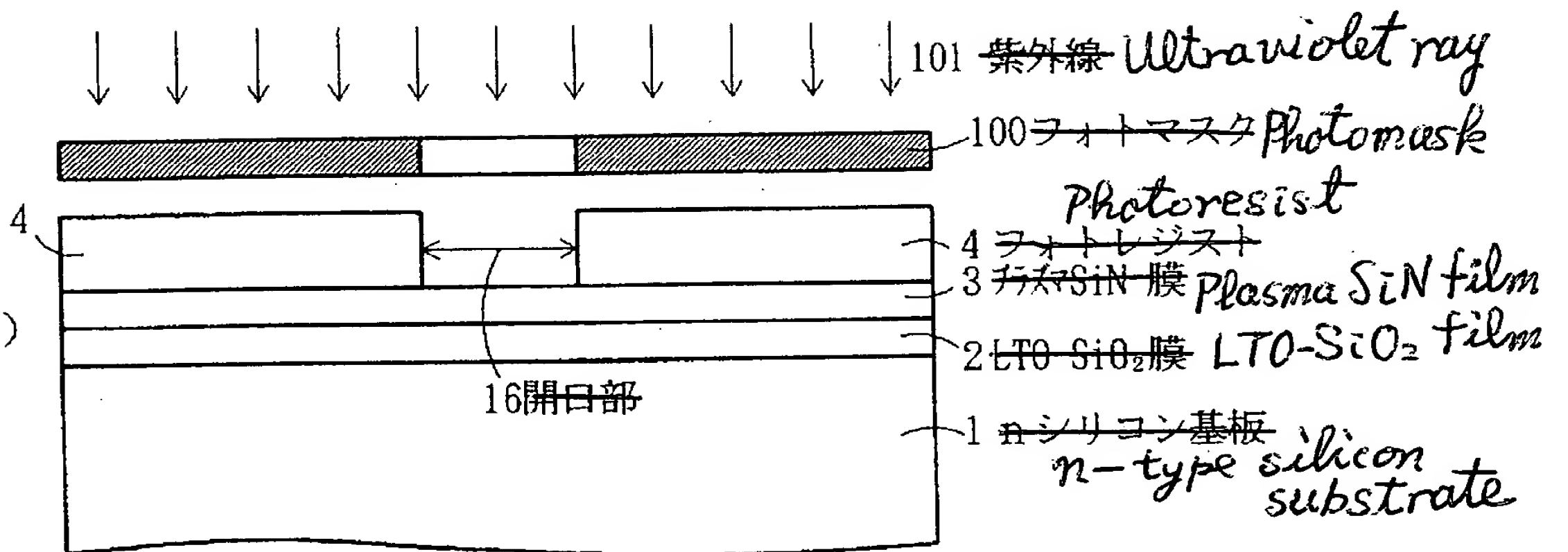


Fig.17(b)

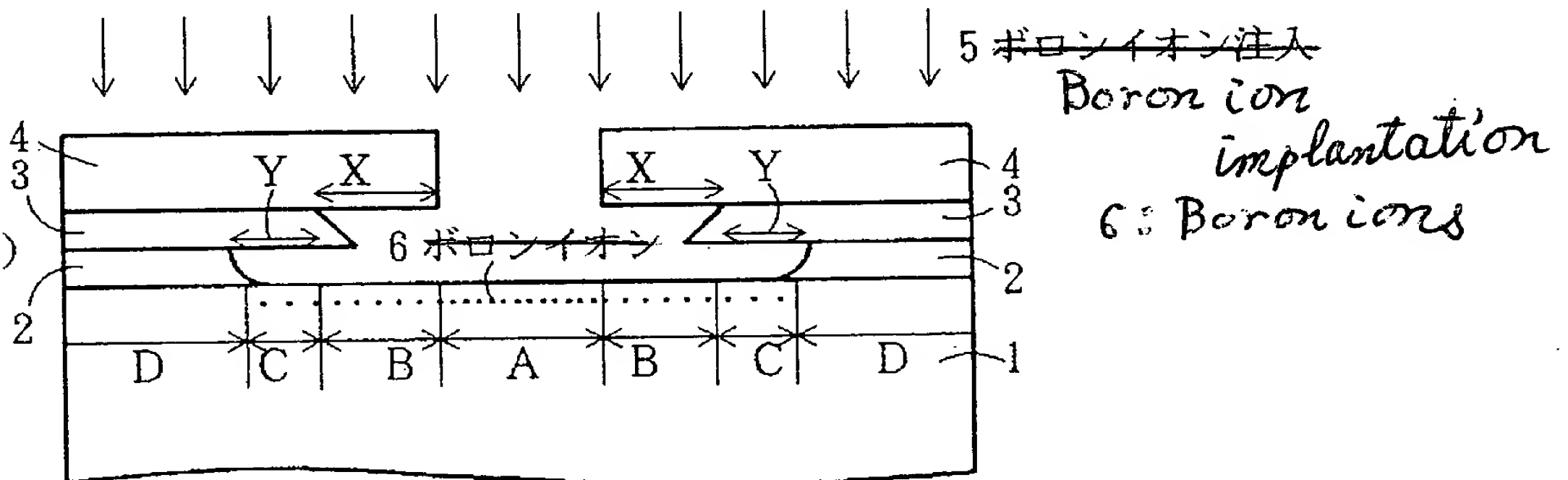


Fig.17(c)

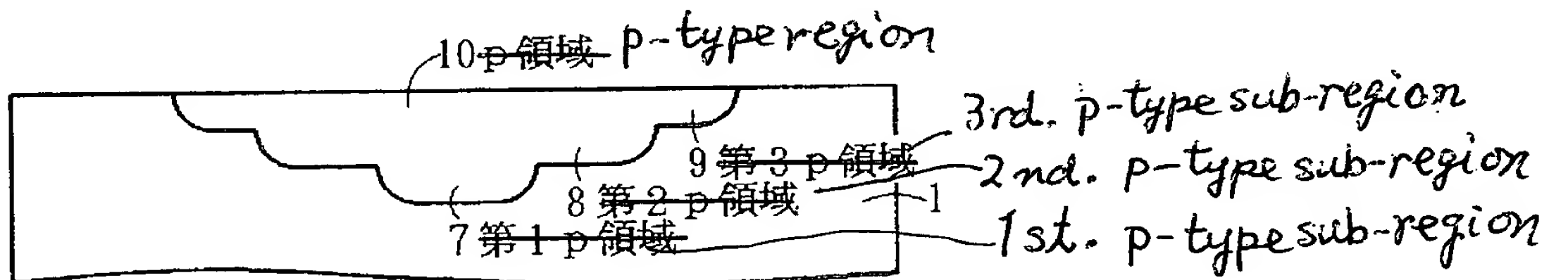


Fig.17(d)

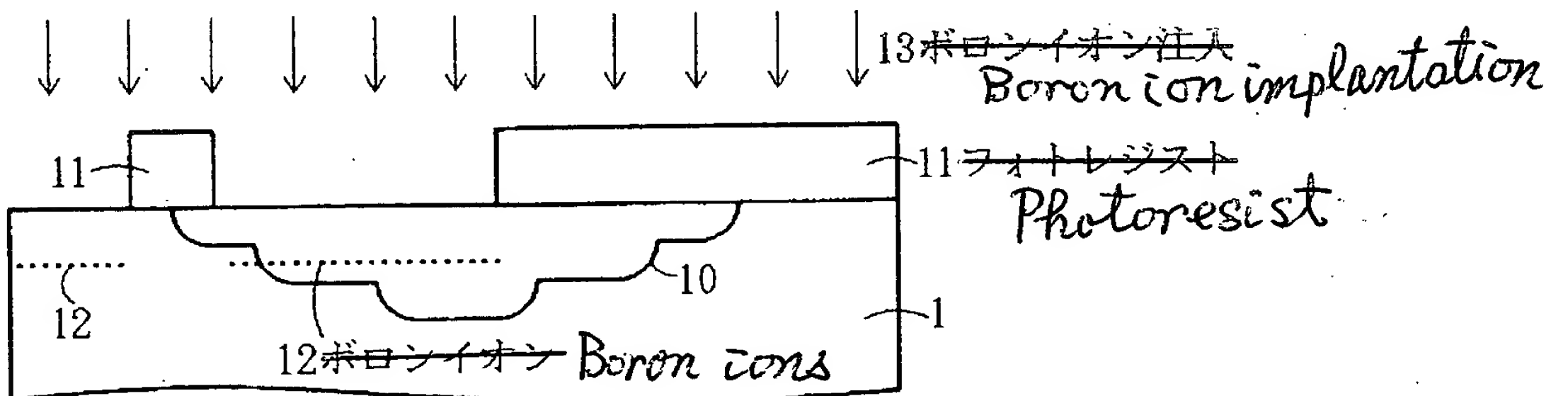
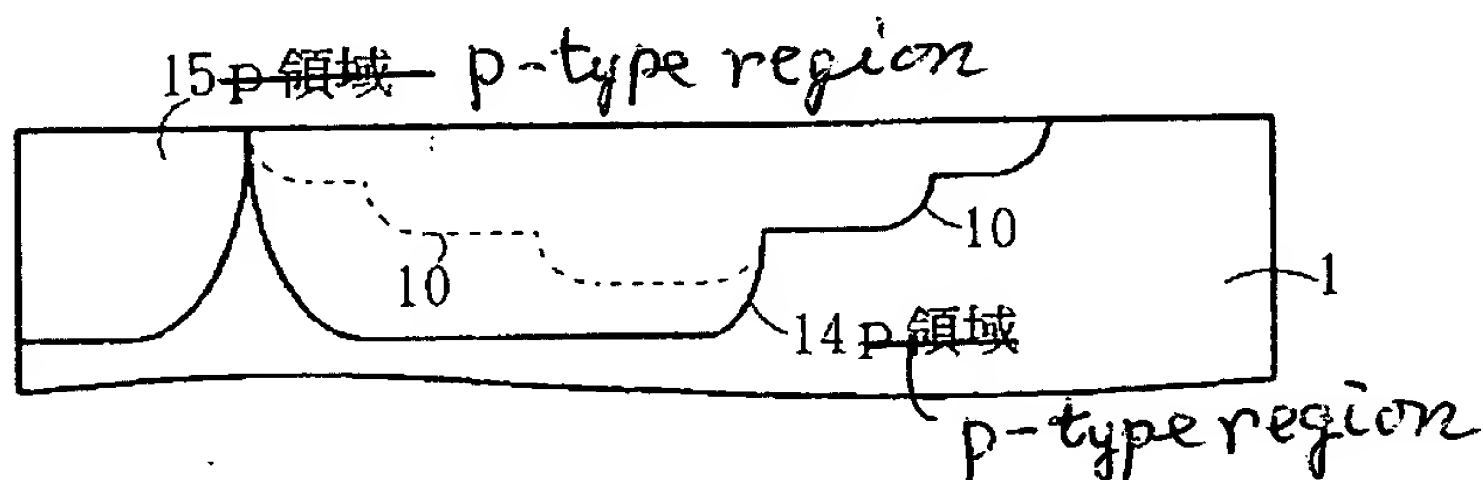


Fig.17(e)



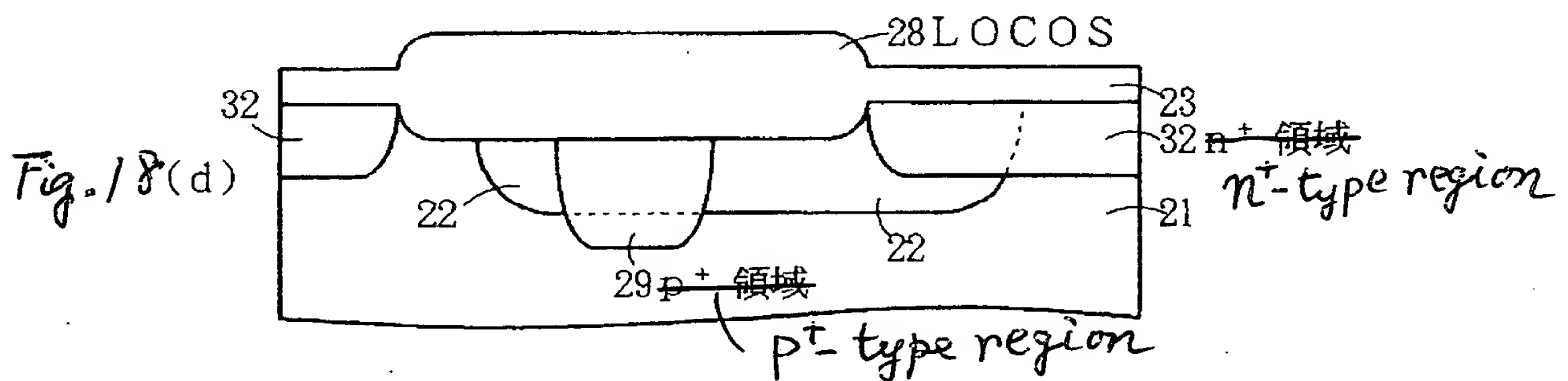
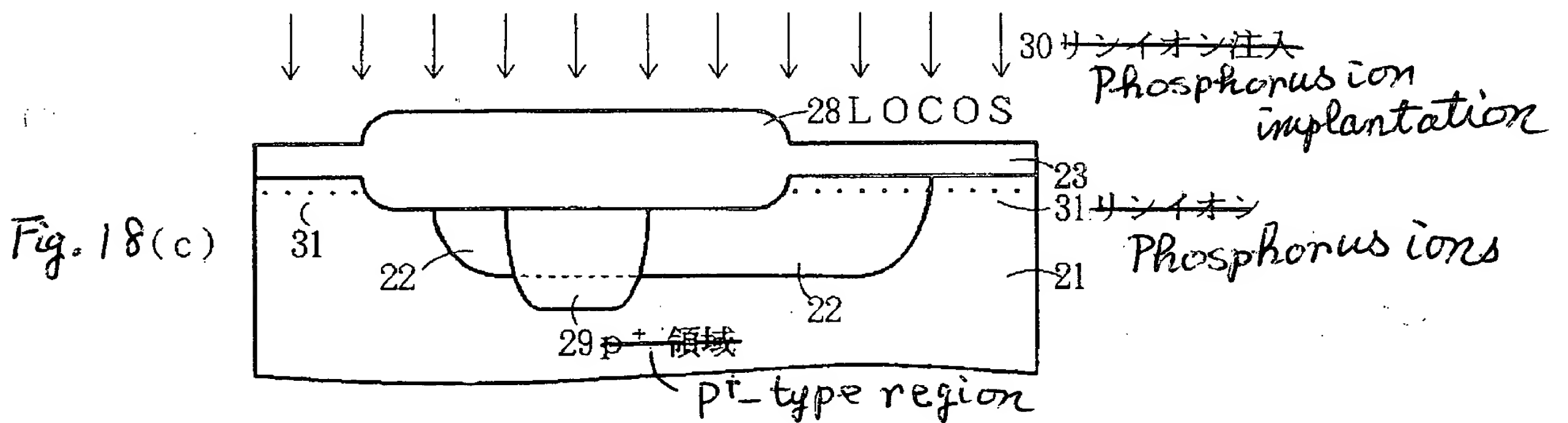
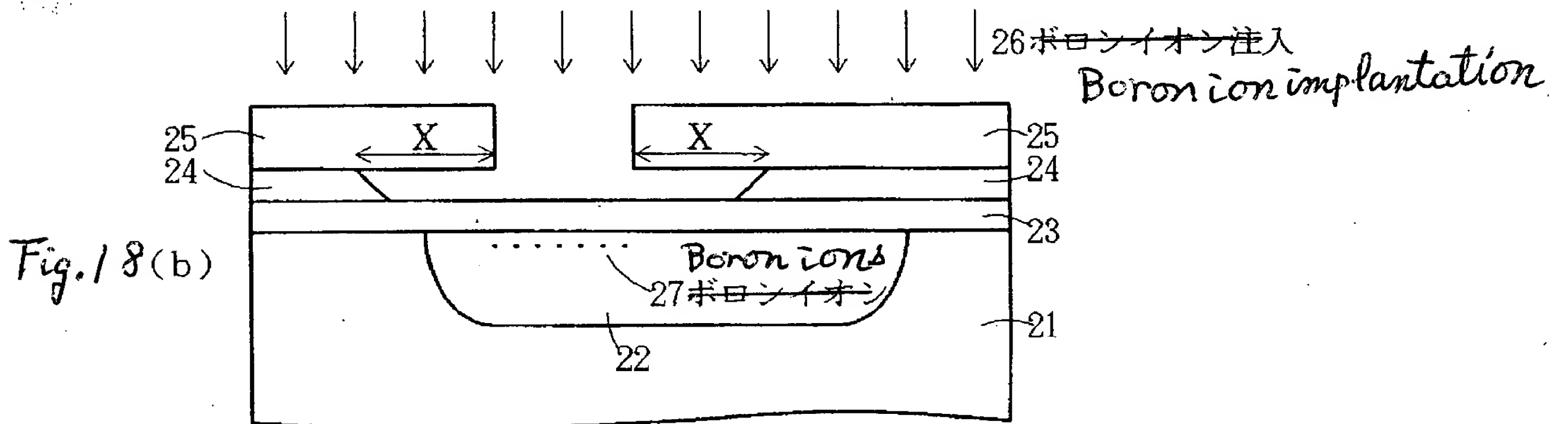
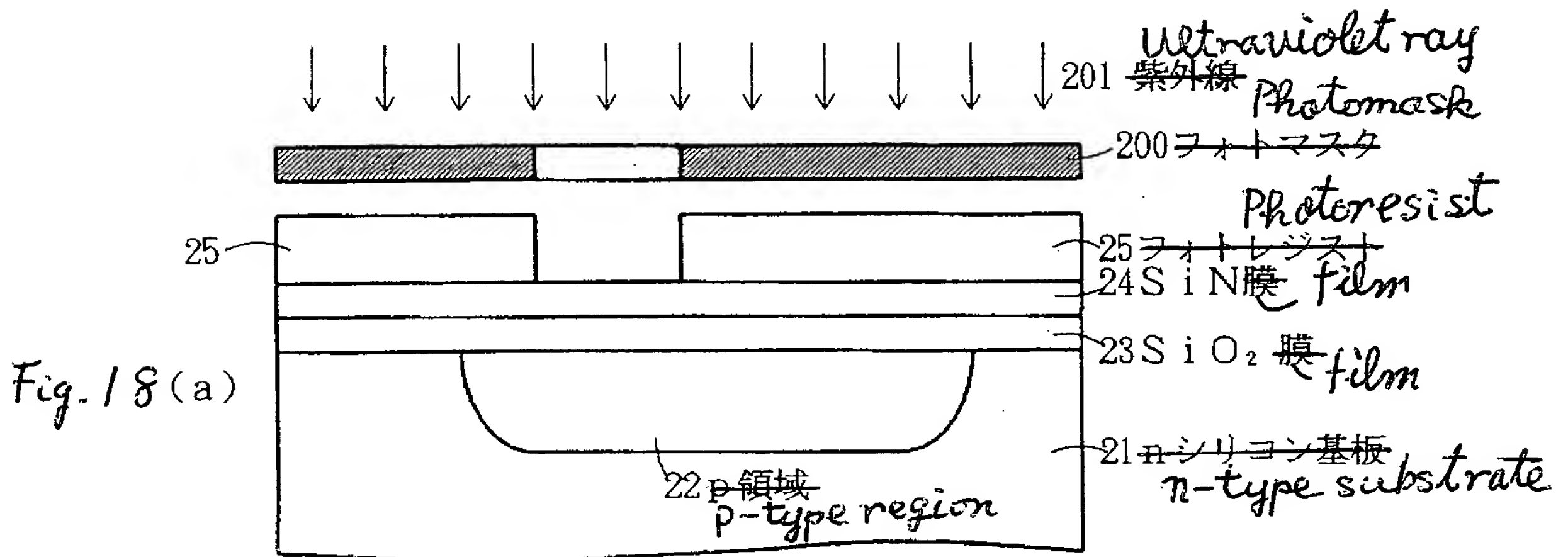


Fig. 19

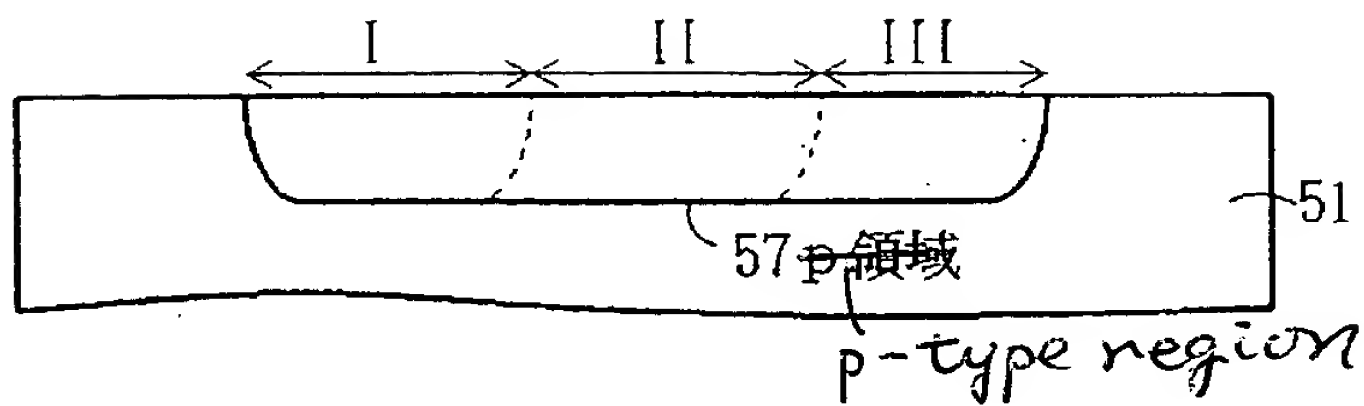


Fig. 20

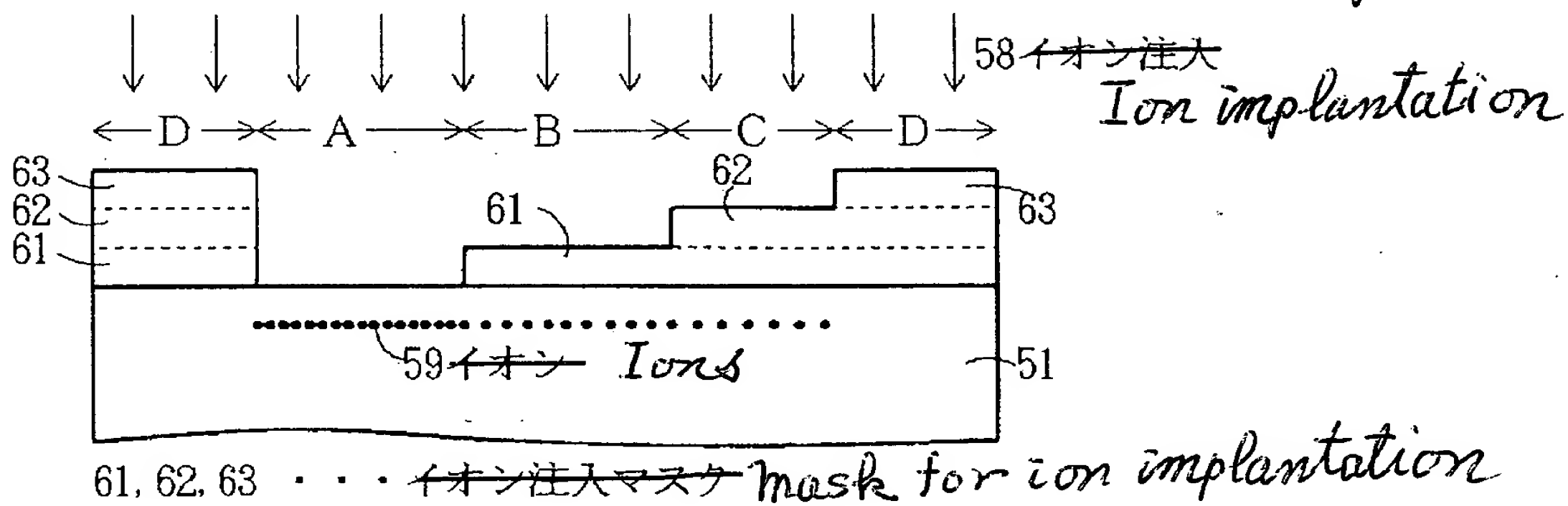
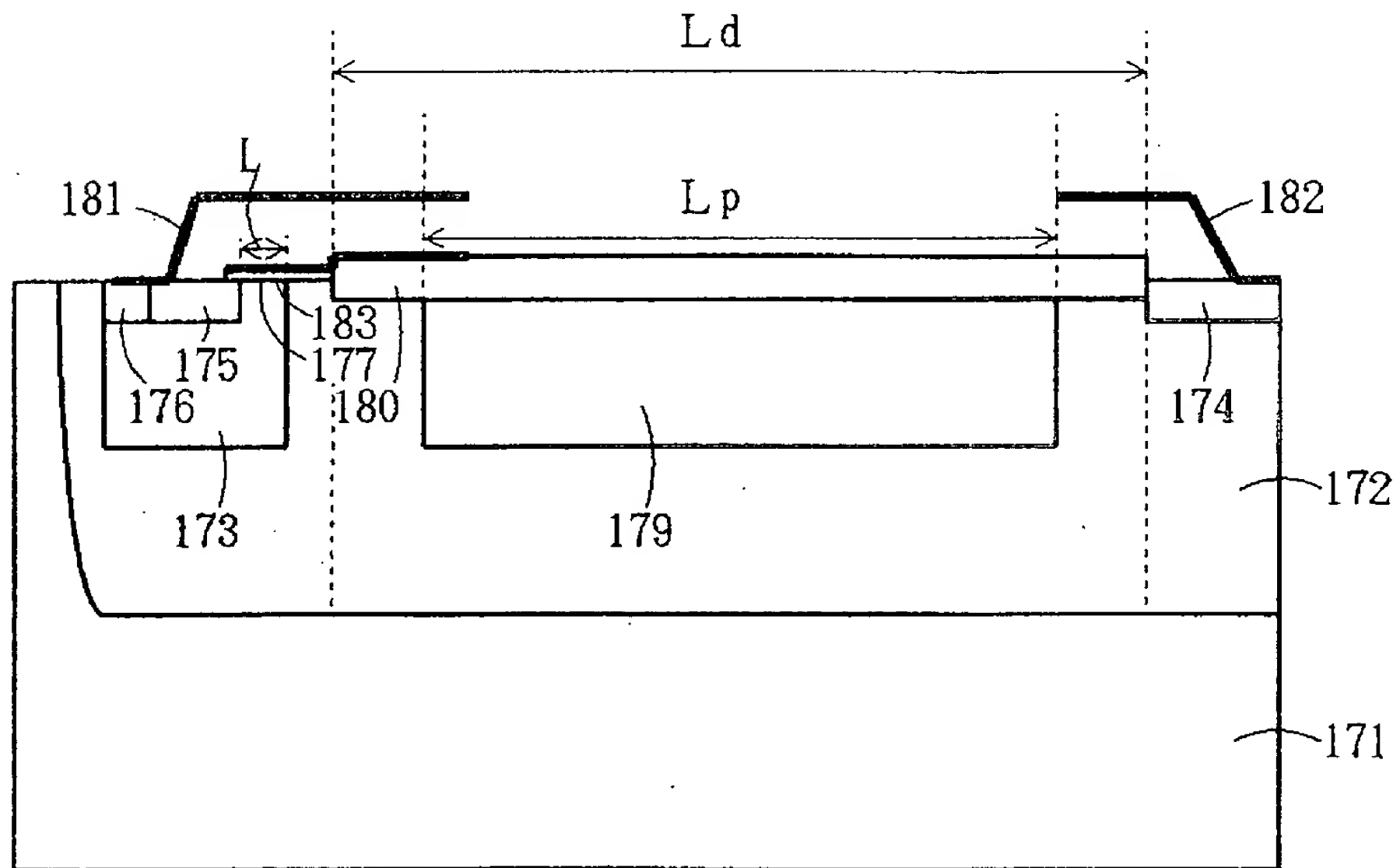


Fig. 21



- | | |
|--|---|
| 171: p-type substrate | 177: Gate electrode |
| 172: n-type well region | 179: p-type diffusion region (p-type offset region) |
| 173: p-type base region | 180: Insulation film |
| 174: n-type drain region | 181: Source electrode |
| 175: n-type source region | 182: Drain electrode |
| 176: p ⁺ -type contact region | 183: Gate oxide film |

Fig. 22(a)

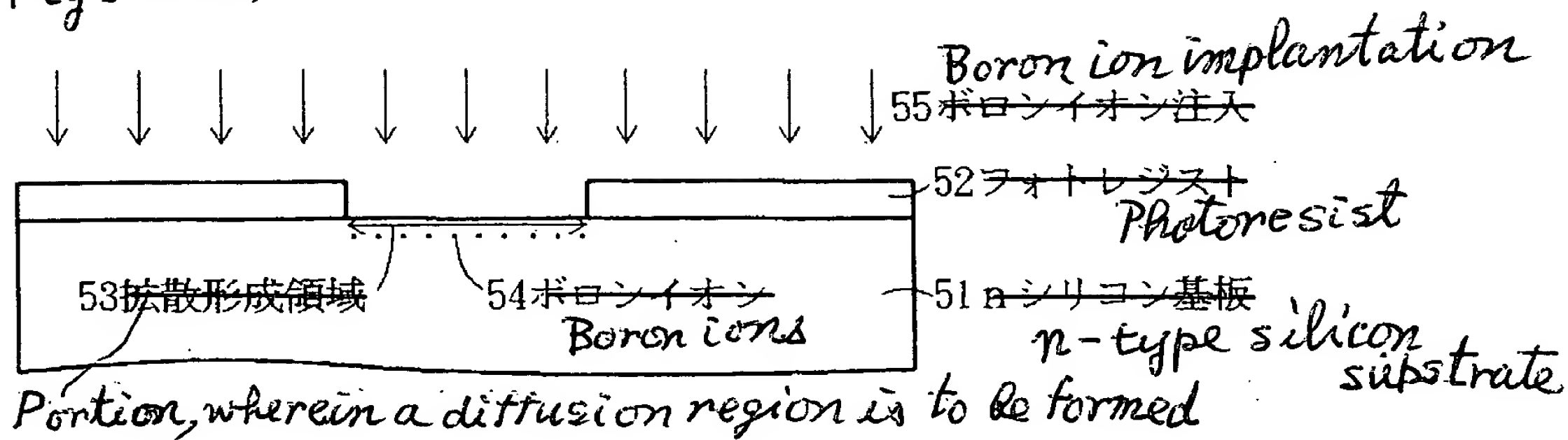


Fig. 22(b)

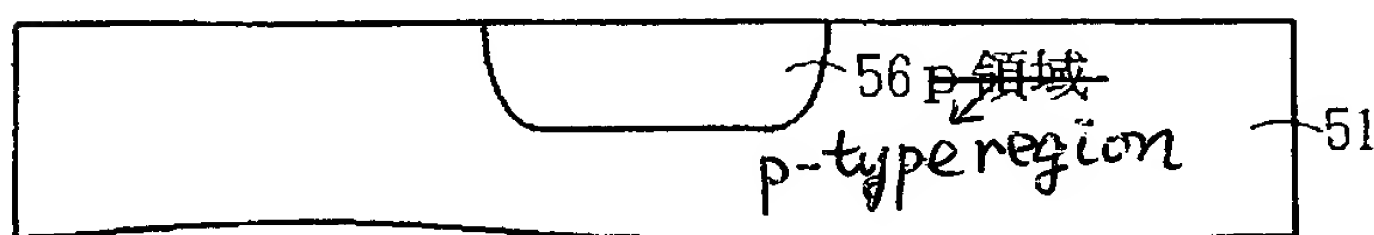
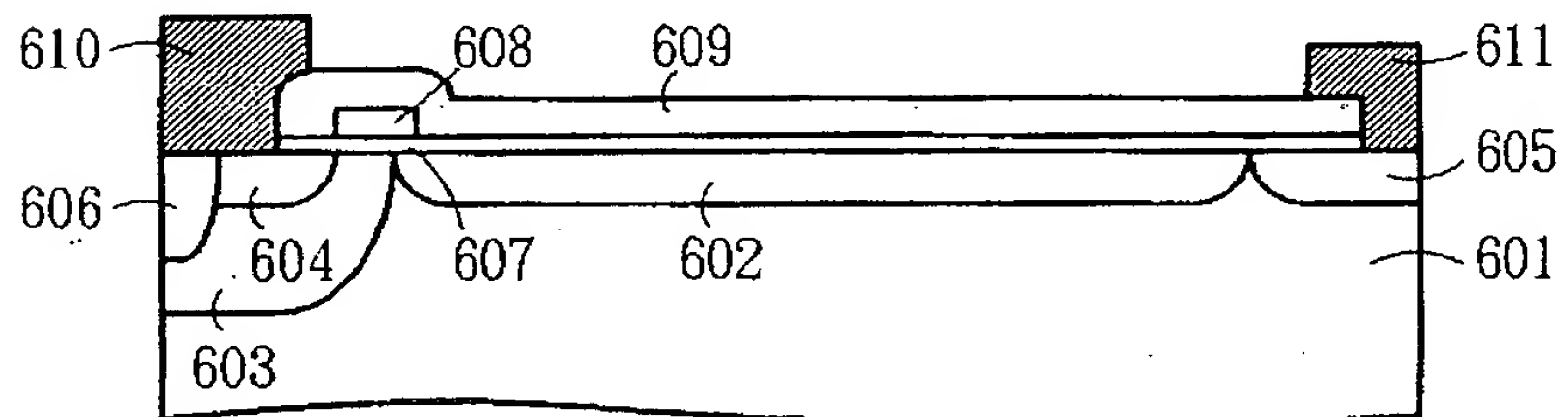


Fig. 23



- 601: n-type silicon substrate
- 602: p-type region (p-type offset region)
- 603: p-type region (p-type base region)
- 604: n-type source region
- 605: n-type drain region
- 606: p-type contact region

- 607: Gate oxide film
- 608: Gate electrode
- 609: Insulation film
- 610: Source electrode
- 611: Drain electrode

Fig. 24

